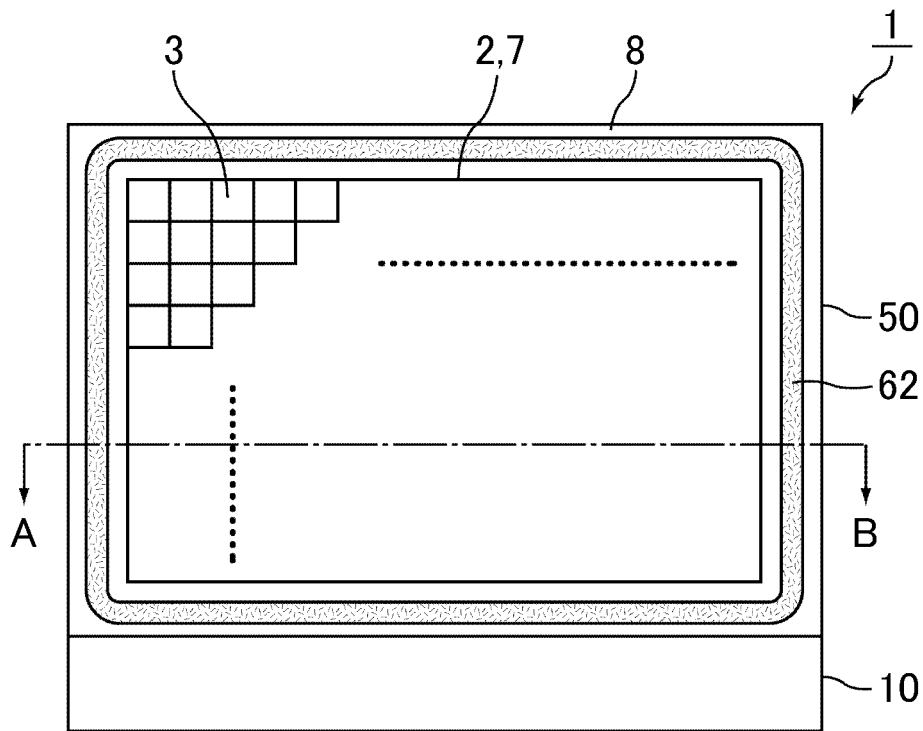
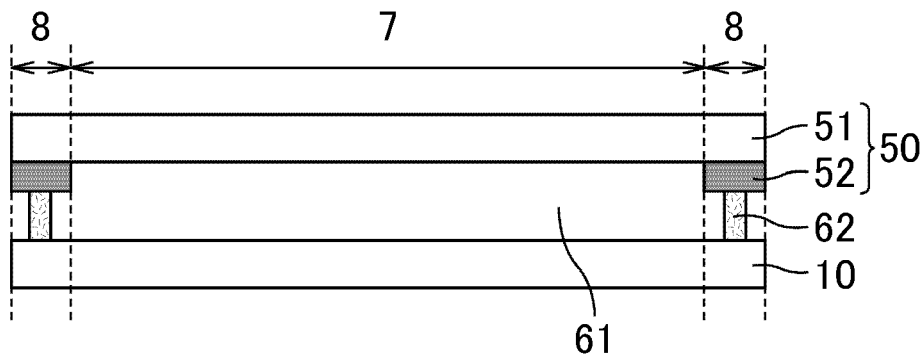


[図1]

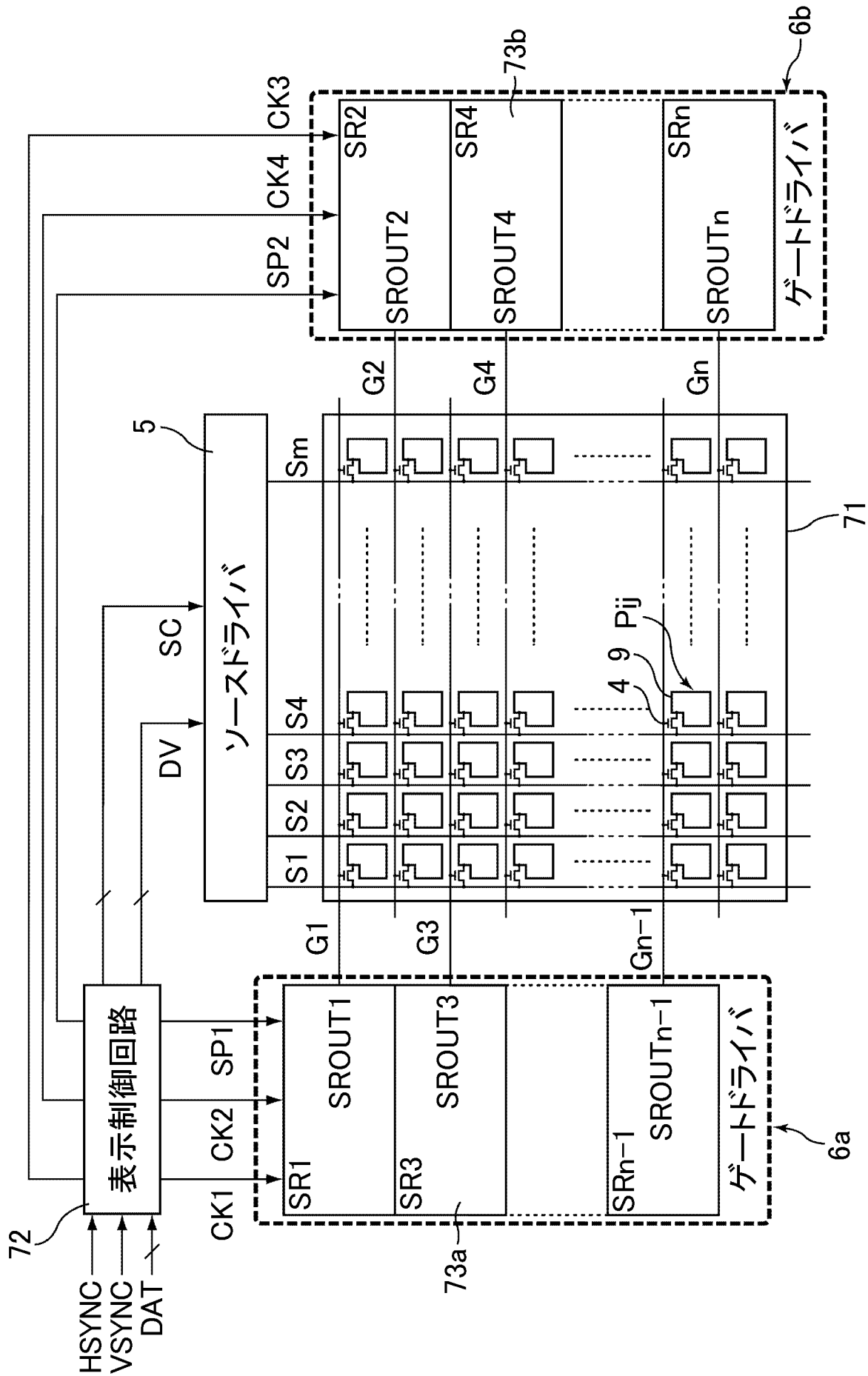


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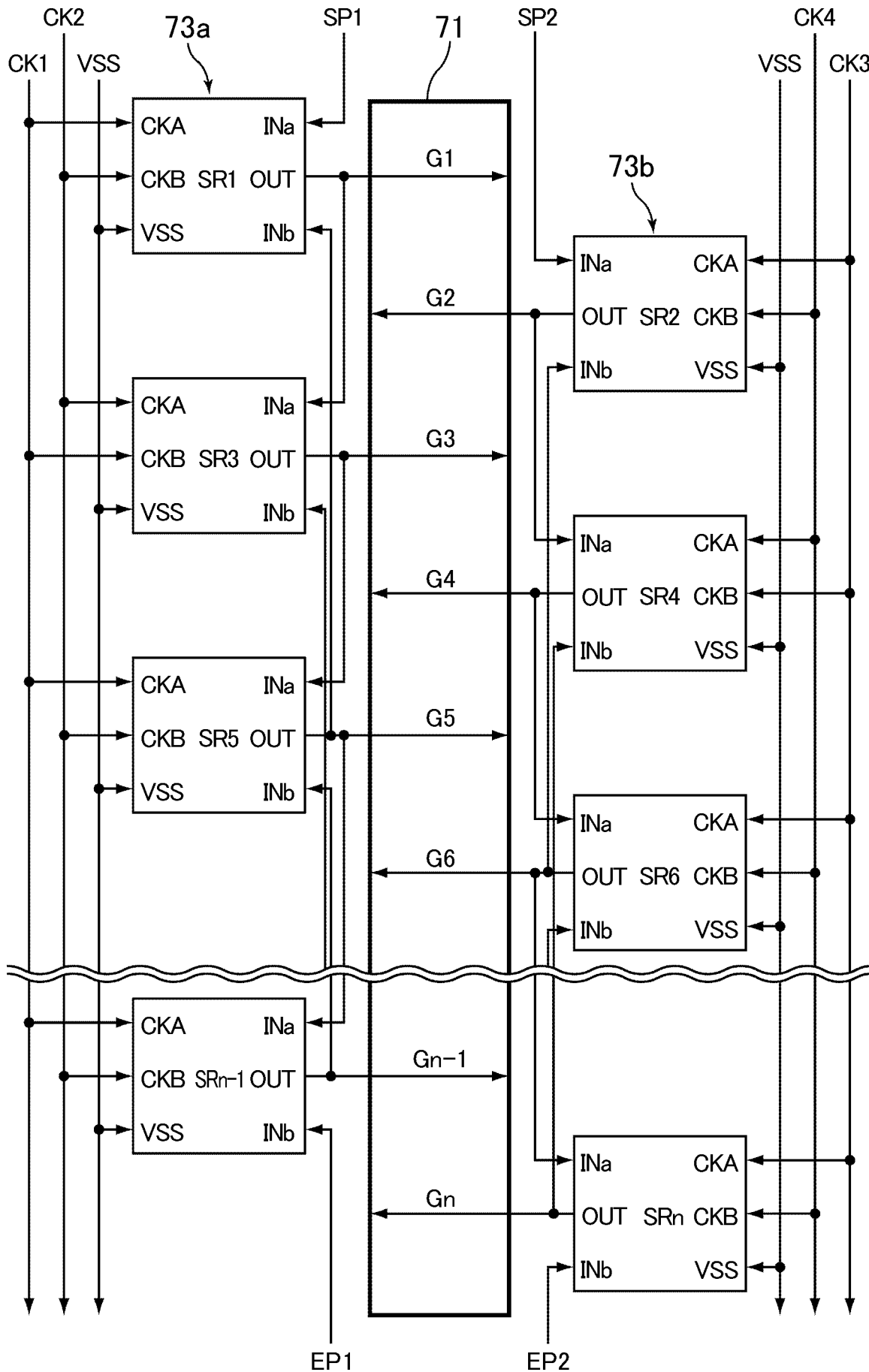




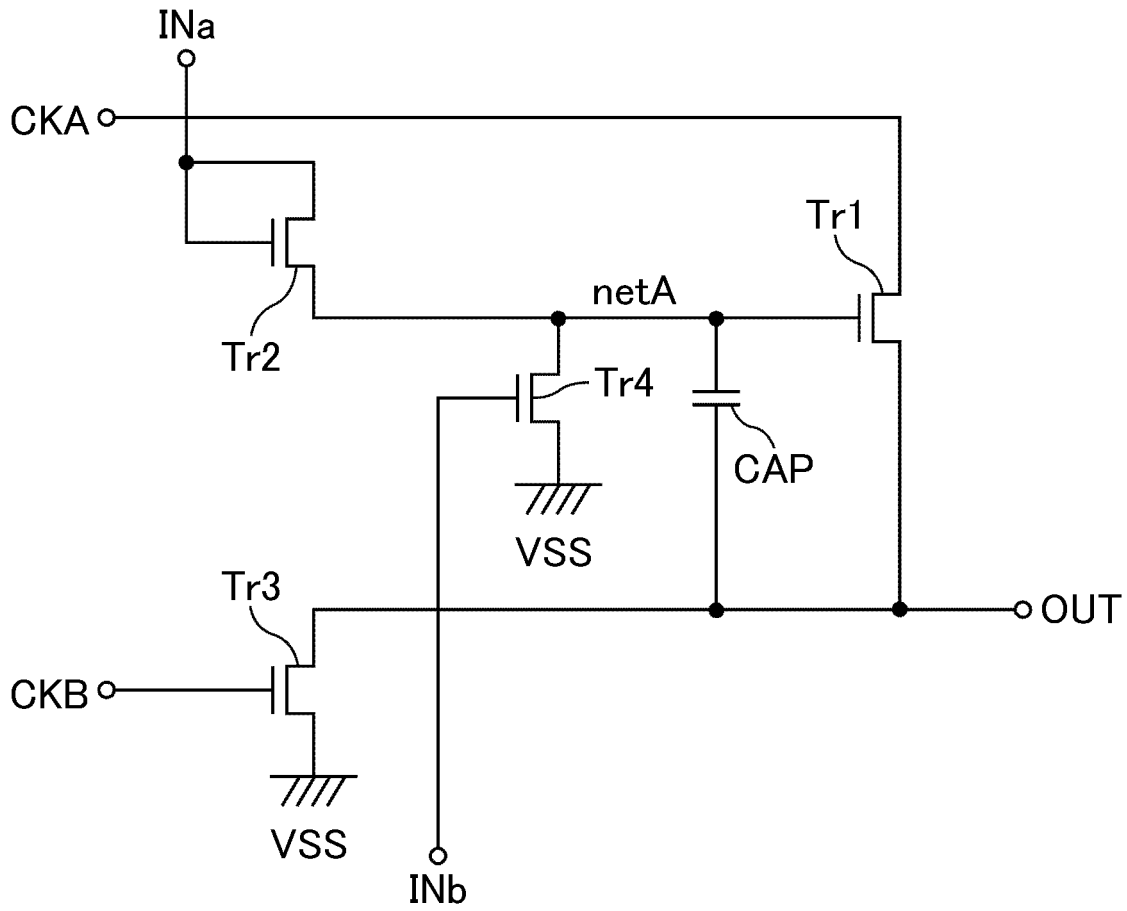
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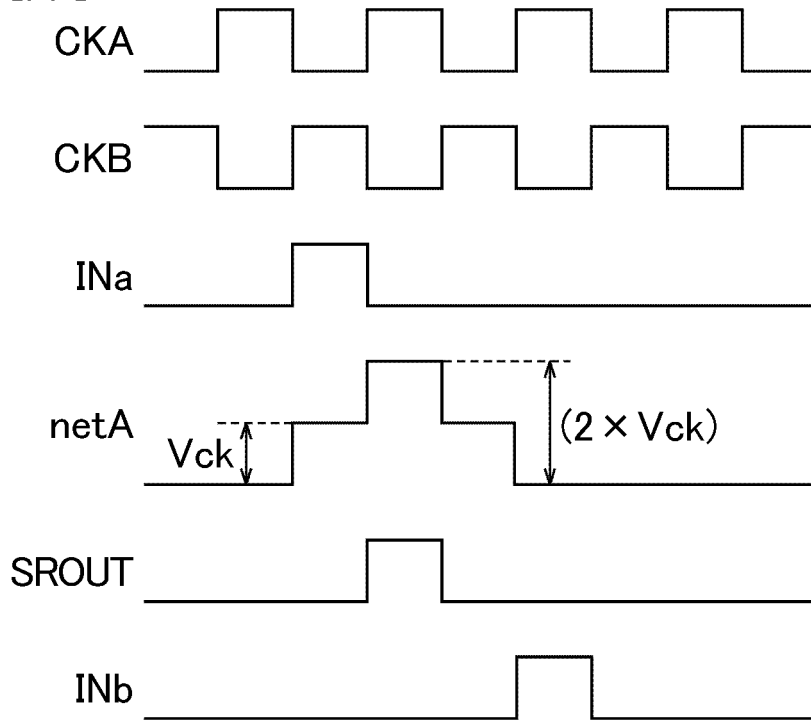
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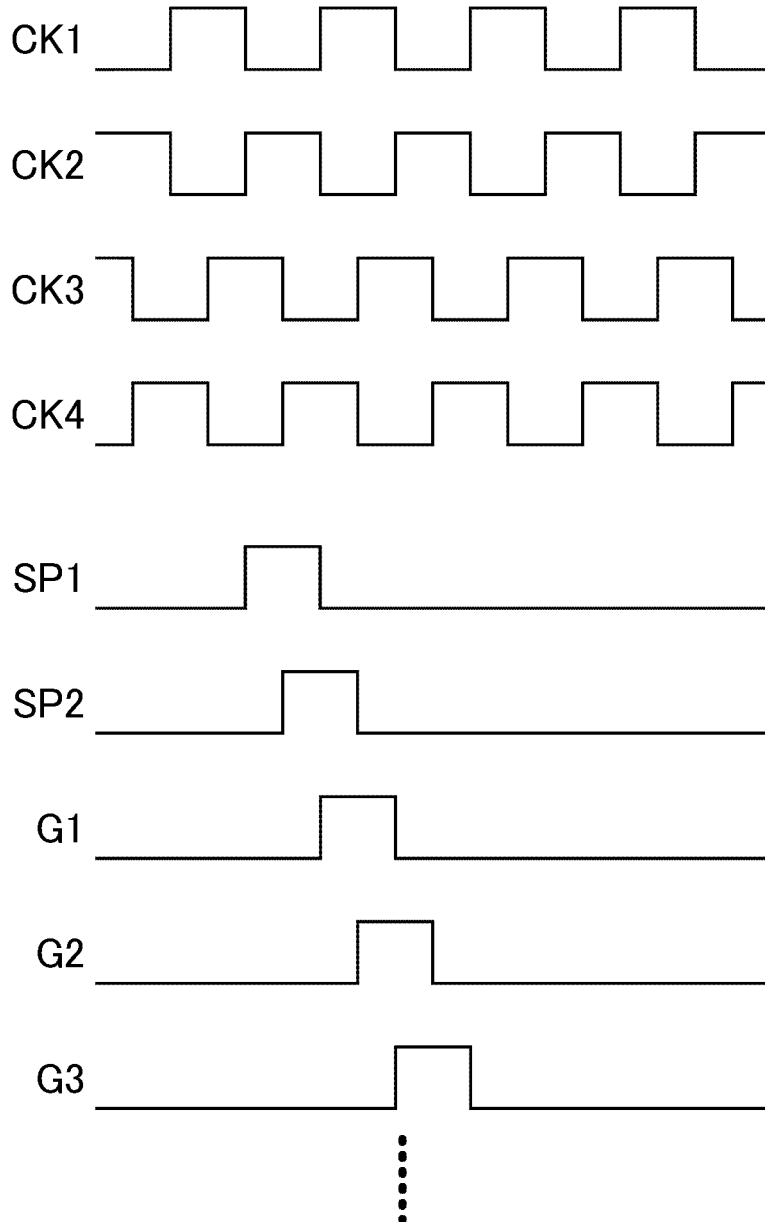
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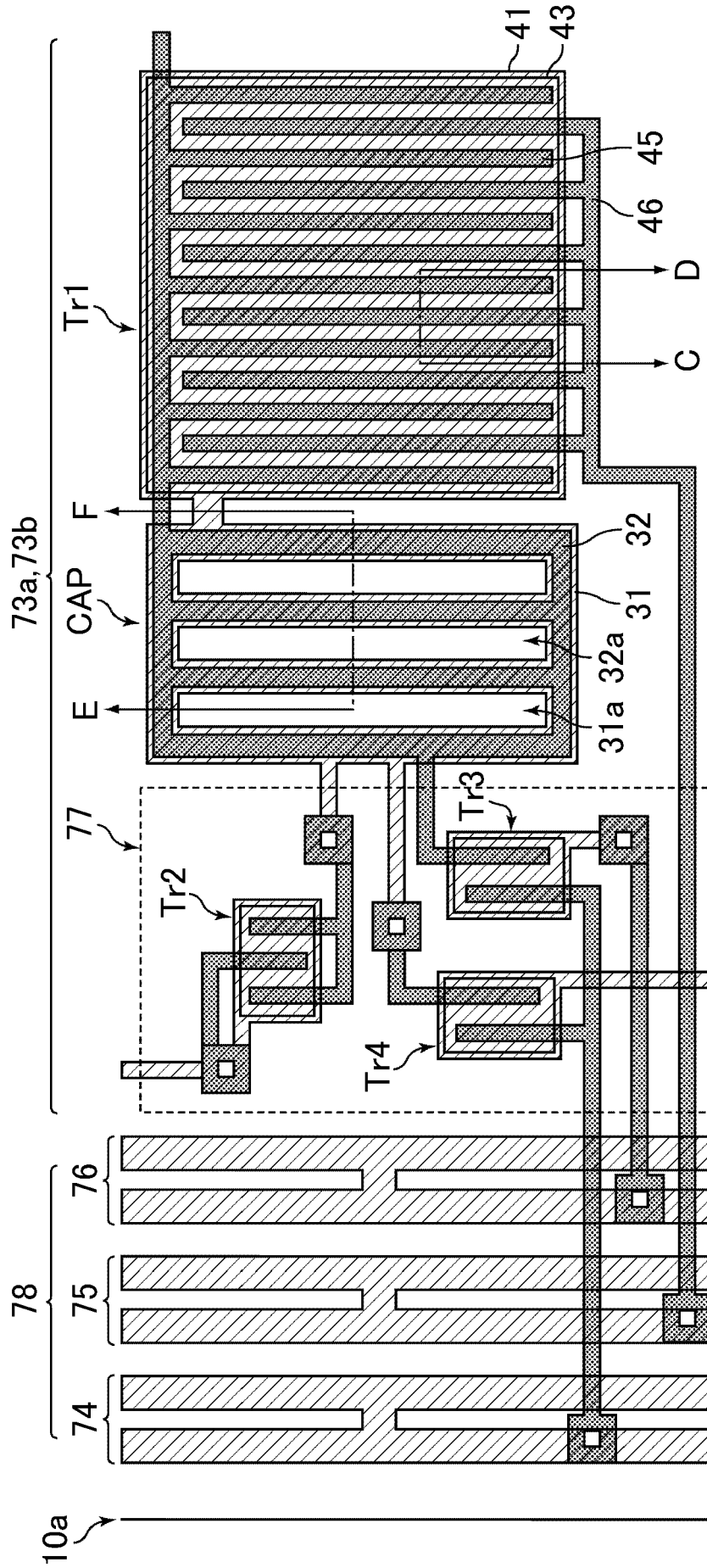
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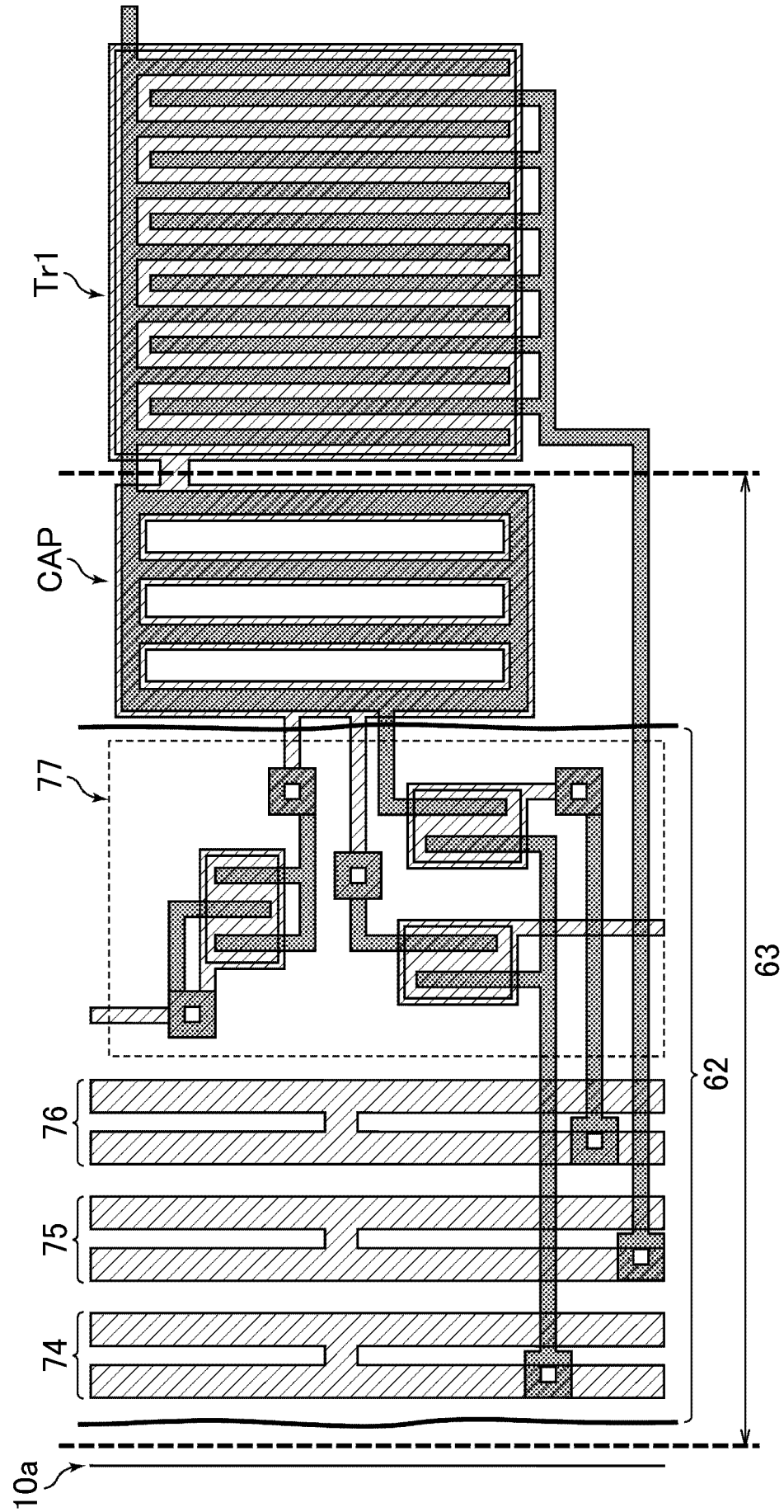
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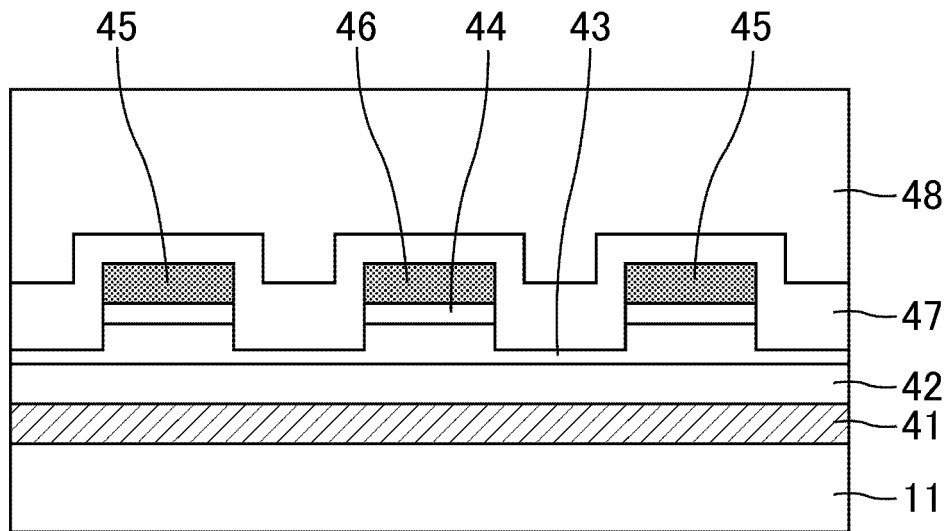
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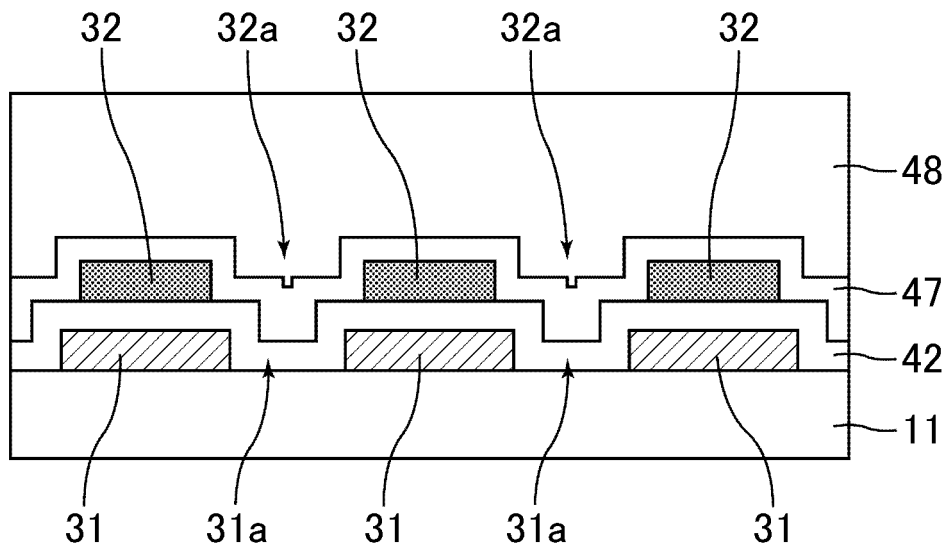
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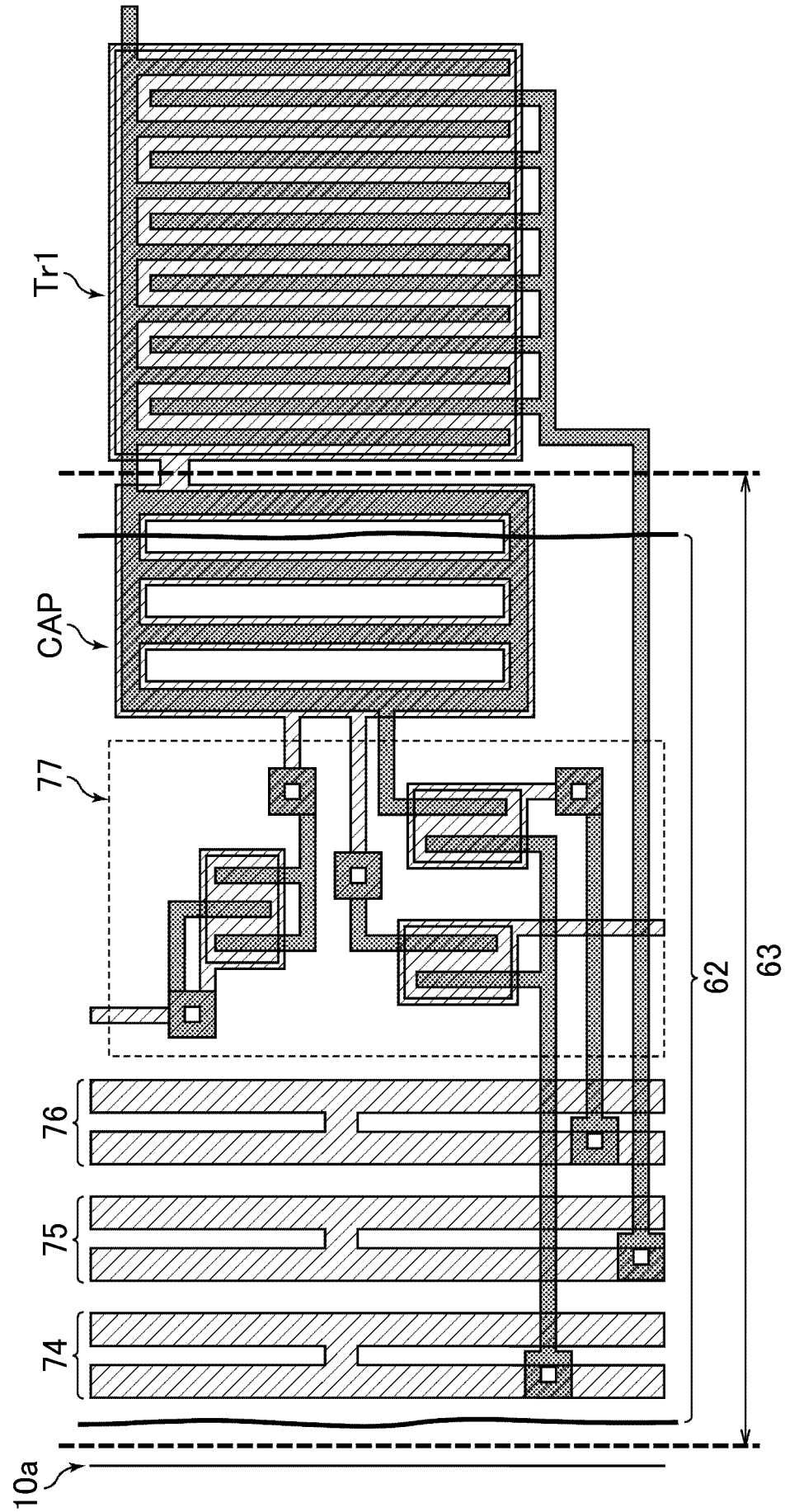
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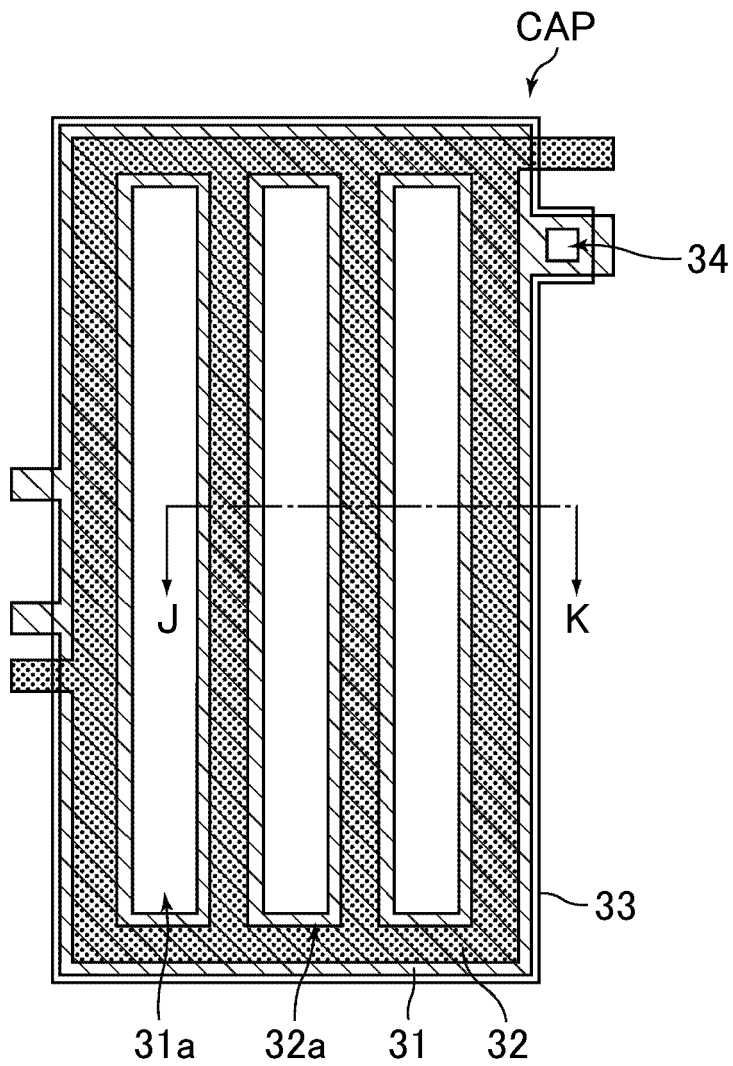
[図12]



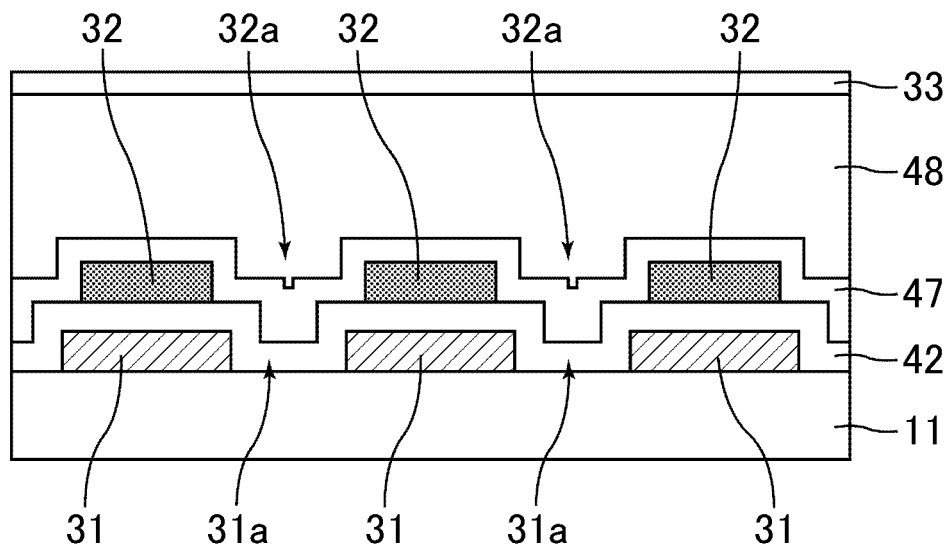
[図13]



[図14]

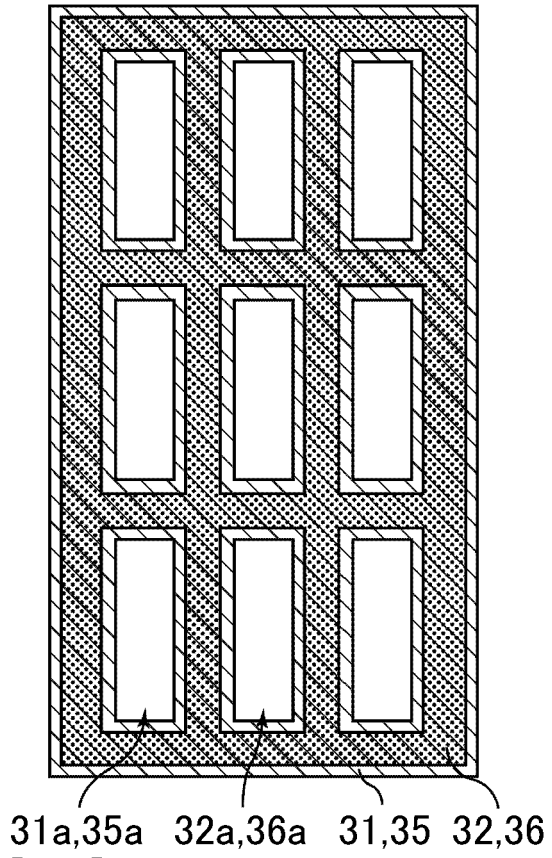


[図15]

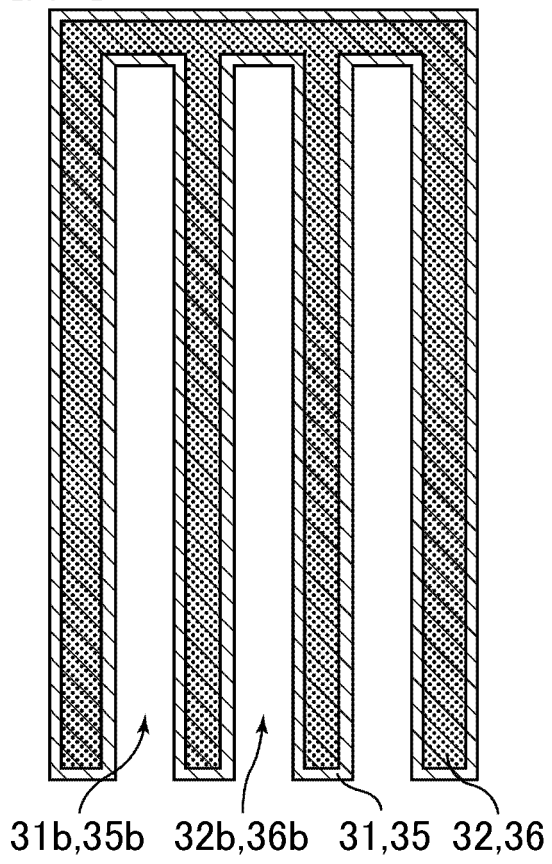




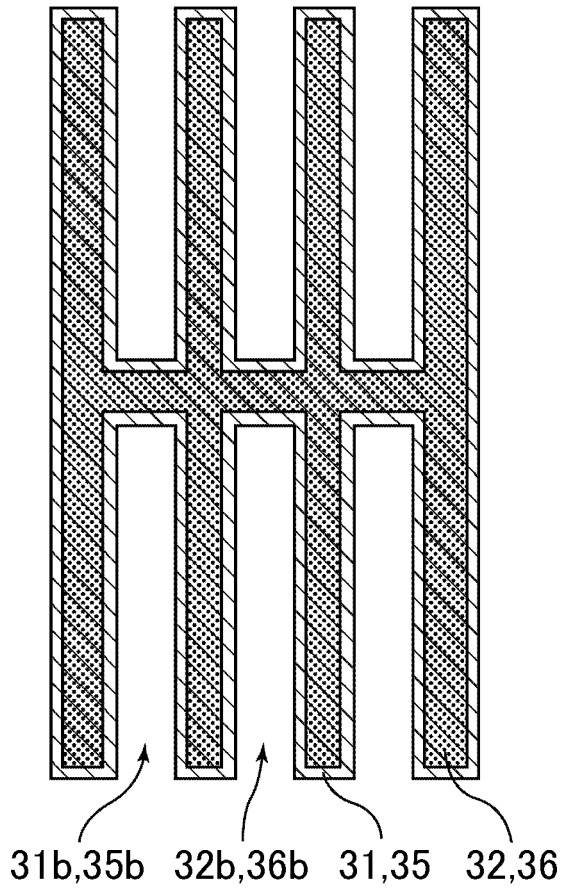
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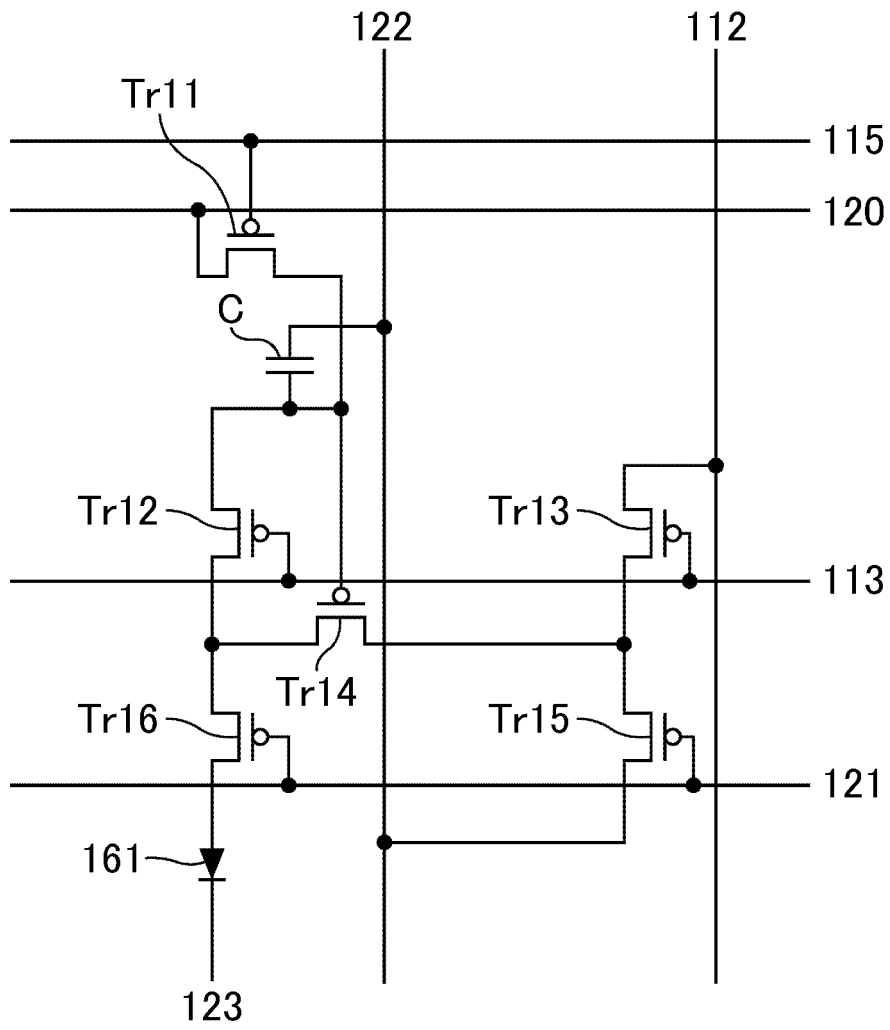
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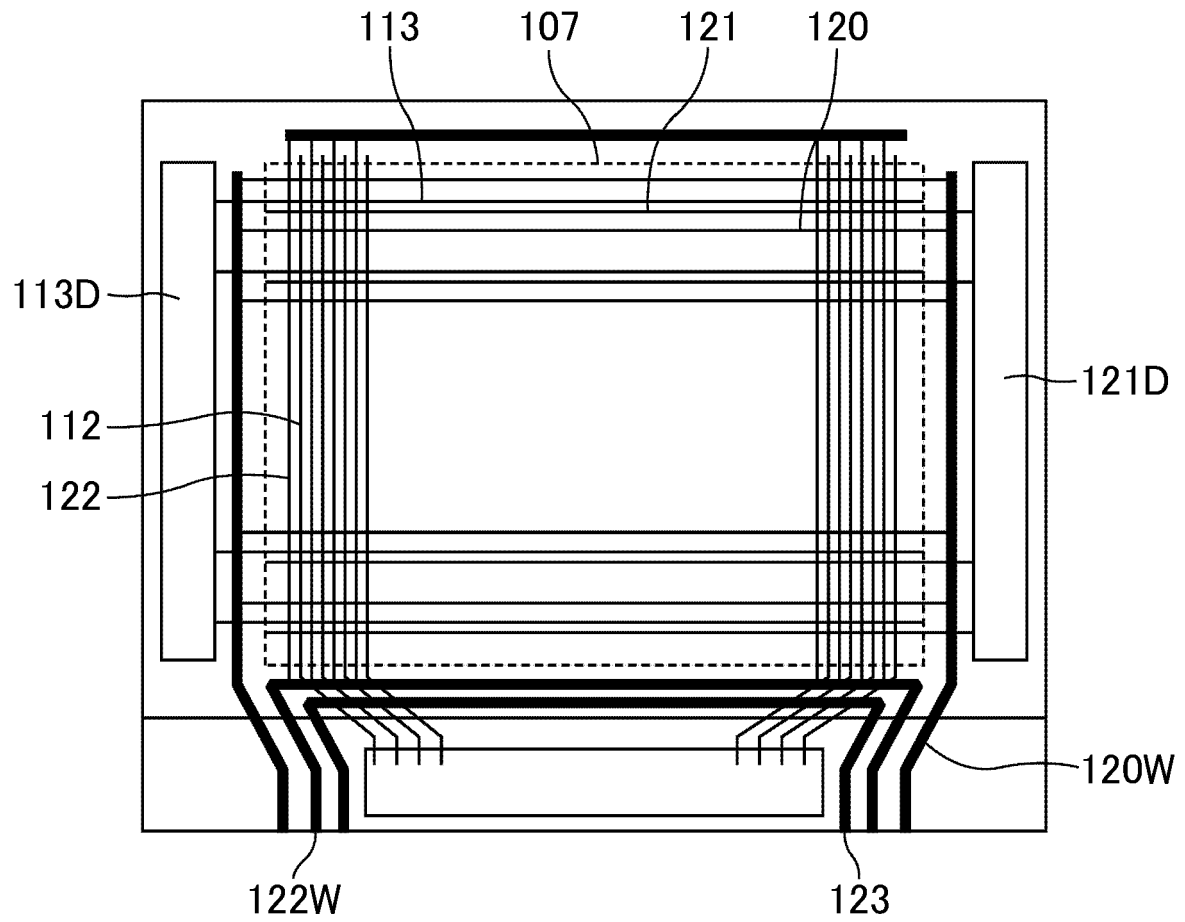
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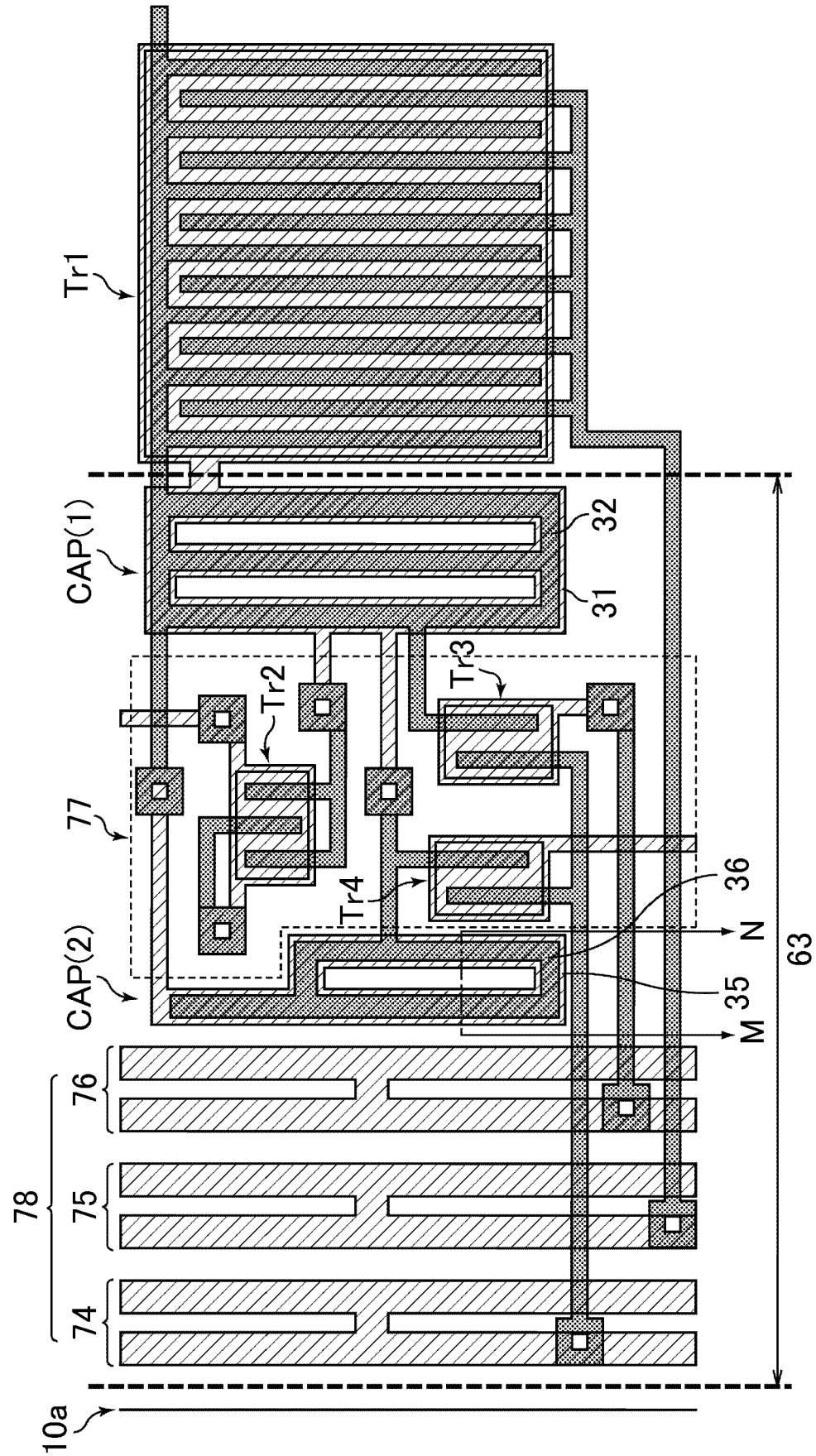
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[図21]

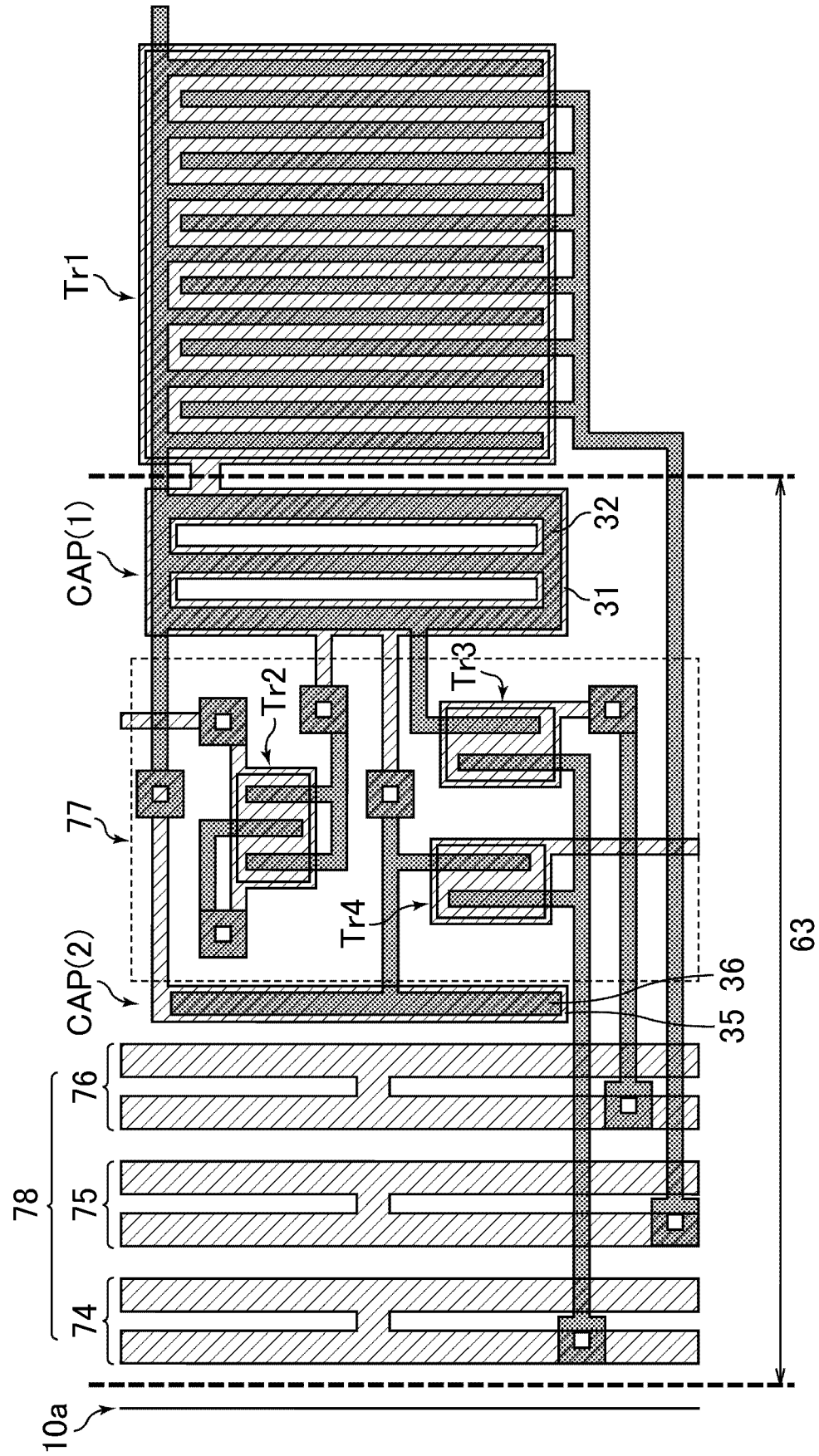


[図22]



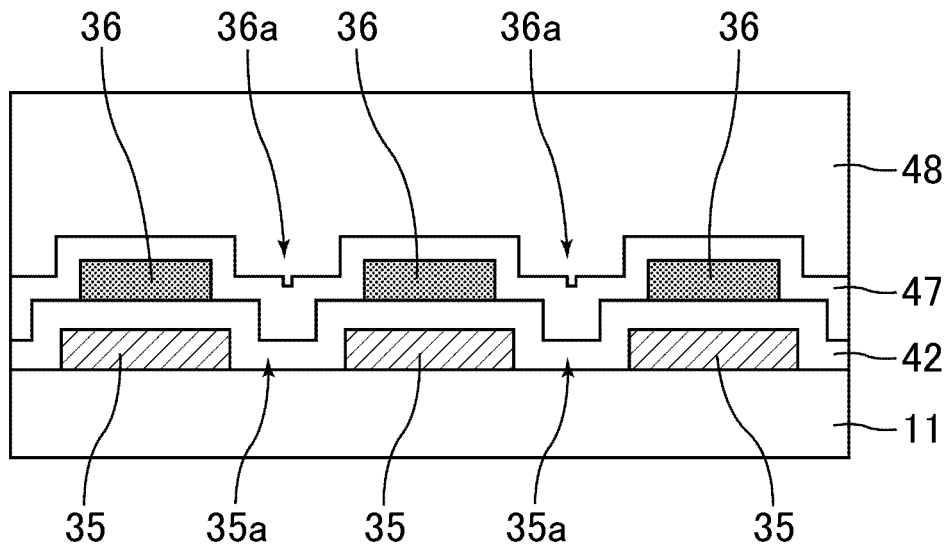
A cross-sectional view of a semiconductor device. The device consists of a substrate 11, a first layer 35, a second layer 42, a third layer 47, and a fourth layer 48. A trench 35a is formed in the first layer 35, extending through the second layer 42 and the third layer 47. The trench 35a is filled with a material 36a. The top surface of the trench 35a is covered by the fourth layer 48. The top surface of the trench 35a is also covered by a material 36. The top surface of the trench 35a is also covered by a material 36.

[図24]



[illegible]

[図26]



[図27]

